

MITSUBISHI IGBT MODULES  
**CM75RL-24NF**

HIGH POWER SWITCHING USE

**CM75RL-24NF**



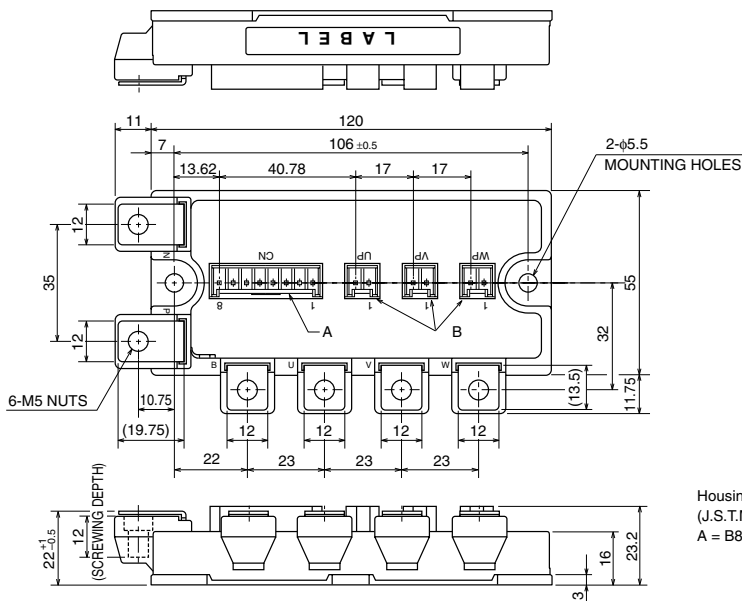
- IC ..... 75A
- VCES ..... 1200V
- Insulated Type
- 7-elements in a pack

**APPLICATION**

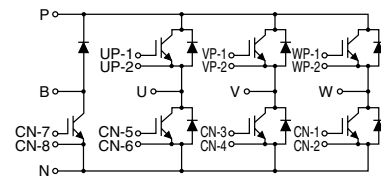
AC drive inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



Housing Type of A and B  
 (J.S.T.Mfg.Co.Ltd)  
 A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

**CM75RL-24NF**

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**ABSOLUTE MAXIMUM RATINGS (T<sub>j</sub> = 25°C, unless otherwise specified)**

**INVERTER PART**

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	1200	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>c</sub> = 87°C*1	75	A
I <sub>CM</sub>		Pulse (Note 2)	150	A
I <sub>E</sub> (Note 1)	Emitter current		75	A
I <sub>EM</sub> (Note 1)		Pulse (Note 2)	150	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>c</sub> = 25°C	520	W

**BRAKE PART**

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	1200	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>c</sub> = 94°C*1	50	A
I <sub>CM</sub>		Pulse (Note 2)	100	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>c</sub> = 25°C	390	W
V <sub>RRM</sub>	Repetitive peak reverse voltage	Clamp diode part	1200	V
I <sub>FM</sub>	Forward current	Clamp diode part	50	A

**(COMMON RATING)**

Symbol	Parameter	Conditions	Ratings	Unit
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>iso</sub>	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	2500	V <sub>rms</sub>
—	Torque strength	Main terminals M5 screw	2.5 ~ 3.5	N • m
—		Mounting M5 screw	2.5 ~ 3.5	N • m
—	Weight	Typical value	350	g

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise specified)**  
**INVERTER PART**

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA	
VGE(th)	Gate-emitter threshold voltage	IC = 7.5mA, VCE = 10V	6	7	8	V	
IGES	Gate leakage current	±VGE = VGES, VCE = 0V	—	—	0.5	μA	
VCE(sat)	Collector-emitter saturation voltage	IC = 75A, VGE = 15V	T <sub>j</sub> = 25°C	—	2.1	3.0	V
			T <sub>j</sub> = 125°C	—	2.4	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	11.5	nF	
Coes	Output capacitance		—	—	1.0	nF	
Cres	Reverse transfer capacitance		—	—	0.23	nF	
QG	Total gate charge	VCC = 600V, IC = 75A, VGE = 15V	—	338	—	nC	
td(on)	Turn-on delay time	VCC = 600V, IC = 75A VGE = ±15V RG = 4.2Ω, Inductive load IE = 75A	—	—	100	ns	
tr	Turn-on rise time		—	—	50	ns	
td(off)	Turn-off delay time		—	—	300	ns	
tr	Turn-off fall time		—	—	350	ns	
trr (Note 1)	Reverse recovery time		—	—	120	ns	
Qrr (Note 1)	Reverse recovery charge	—	3	—	μC		
VEC(Note 1)	Emitter-collector voltage	IE = 75A, VGE = 0V	—	—	3.8	V	
Rth(j-c)Q	Thermal resistance	IGBT part (1/6 module) <sup>*1</sup>	—	—	0.24	K/W	
Rth(j-c)R		FWDi part (1/6 module) <sup>*1</sup>	—	—	0.36	K/W	
Rth(c-f)	Contact thermal resistance	Case to heat sink, Thermal compound Applied (1/6 module) <sup>*2</sup>	—	0.085	—	K/W	
RG	External gate resistance		4.2	—	63	Ω	

**BRAKE PART**

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA	
VGE(th)	Gate-emitter threshold voltage	IC = 5.0mA	6	7	8	V	
IGES	Gate leakage current	±VGE = VGES, VCE = 0V	—	—	0.5	μA	
VCE(sat)	Collector-emitter saturation voltage	IC = 50A, VGE = 15V	T <sub>j</sub> = 25°C	—	2.1	3.0	V
			T <sub>j</sub> = 125°C	—	2.4	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	8.5	nF	
Coes	Output capacitance		—	—	0.75	nF	
Cres	Reverse transfer capacitance		—	—	0.17	nF	
QG	Total gate charge	VCC = 600V, IC = 50A, VGE = 15V	—	250	—	nC	
VFM	Forward voltage drop	IF = 50A	—	—	3.8	V	
Rth(j-c)Q	Thermal resistance	IGBT part <sup>*1</sup>	—	—	0.32	K/W	
Rth(j-c)R		Clamp diode part <sup>*1</sup>	—	—	0.43	K/W	
RG	External gate resistance		6.3	—	63	Ω	

\*1 : Case temperature (T<sub>c</sub>) measured point is just under the chips.

If you use this value, Rth(f-a) should be measured just under the chips.

\*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

Note 1. IE, VEC, trr & Qrr represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

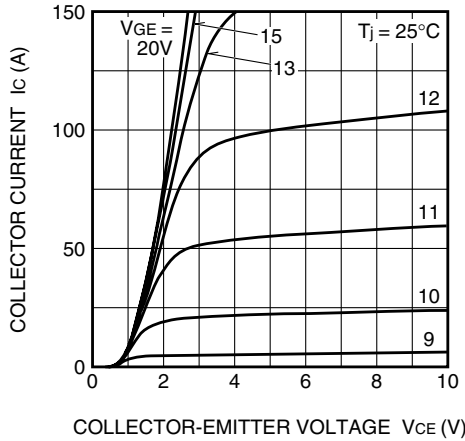
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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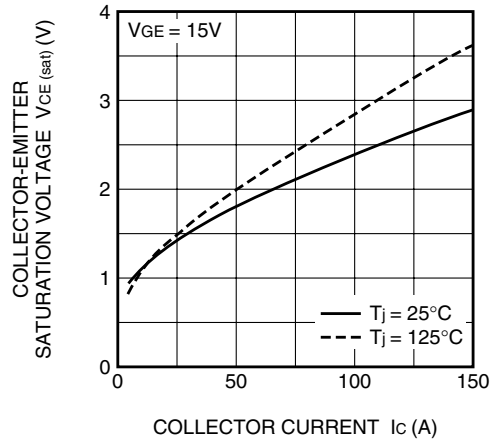
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

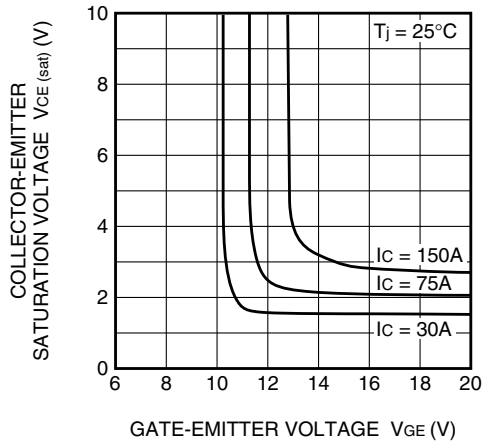
OUTPUT CHARACTERISTICS (TYPICAL)



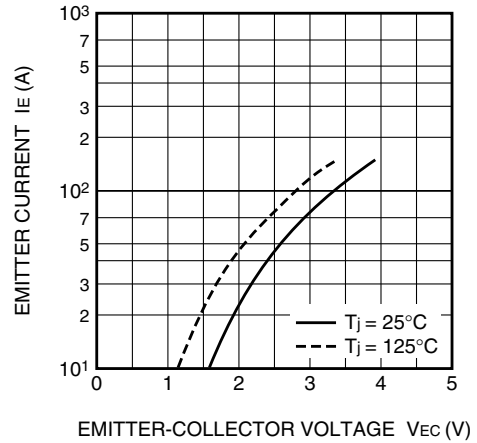
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



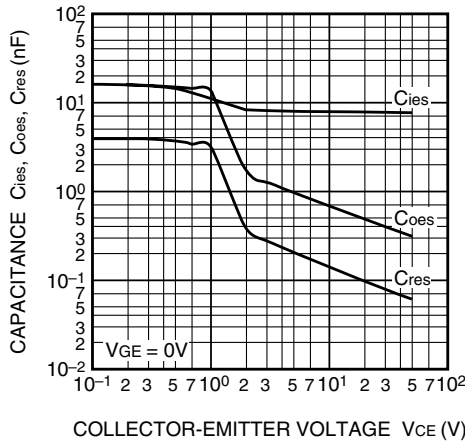
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



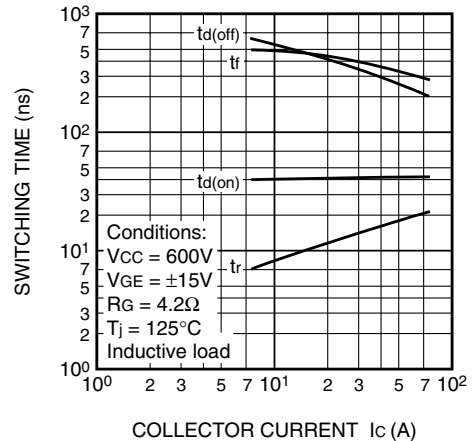
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



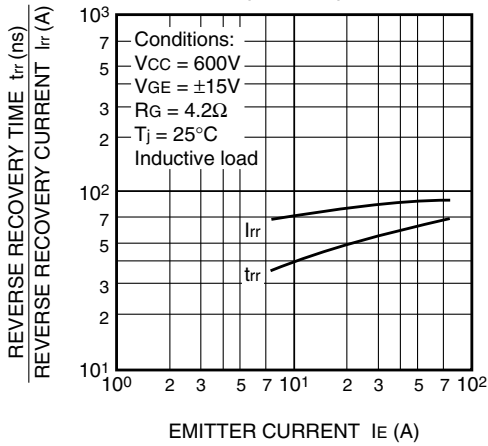
CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)



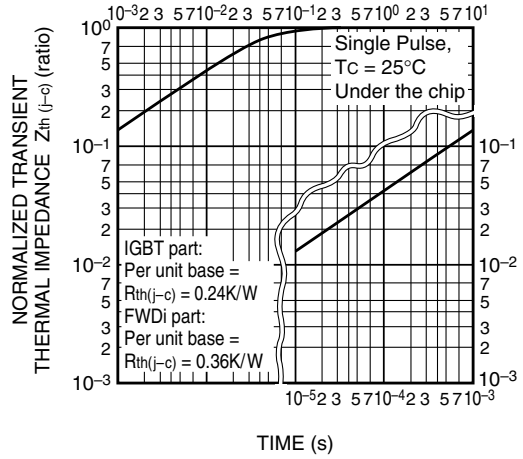
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



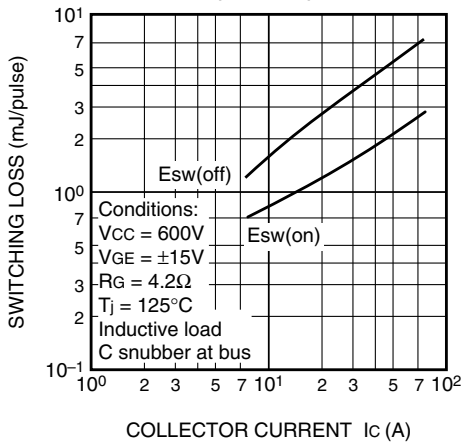
REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



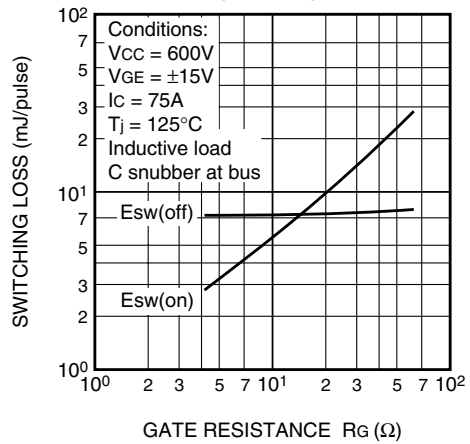
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



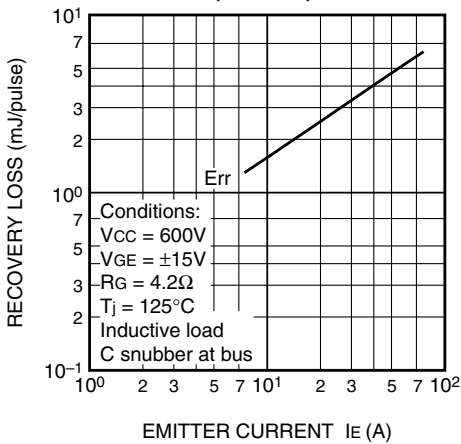
SWITCHING LOSS vs. COLLECTOR CURRENT (TYPICAL)



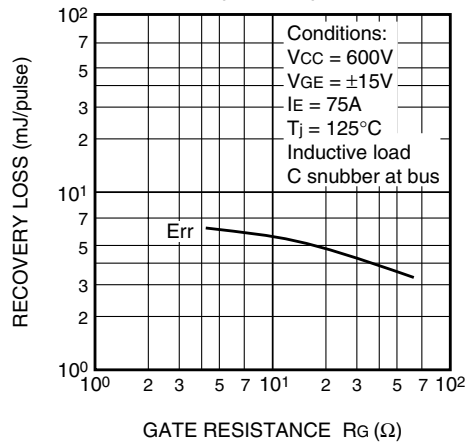
SWITCHING LOSS vs. GATE RESISTANCE (TYPICAL)



RECOVERY LOSS vs. IE (TYPICAL)



RECOVERY LOSS vs. GATE RESISTANCE (TYPICAL)



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